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ΡΛΝ	JIT
	SEMI
	CONDUCTOR

Voltage

Features

PJQ5451E-AU

40V P-Channel Enhancement Mode MOSFET DFN5060-8L -40 V Current -67 A • Rds(on), Vgs@-10V, Id@-20A<9.4mΩ • Rds(ON), Vgs@-4.5V, Id@-10A<14.3mΩ • 100% UIS tested • Reliable and Rugged • AEC-Q101 qualified • Lead free in compliance with EU RoHS 2.0 • Green molding compound as per IEC 61249 standard **Mechanical Data** • Case : DFN5060-8L Package • Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight : 0.08 grams

Maximum Ratings and Thermal Characteristics (TA=25°C unless otherwise noted)

PARAMETE	R	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	±25	V
Continuous Drain Current ^(Note 3)	T _C =25°C		-67	
	Tc=100°C	I _D	-47	А
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-228	
Power Dissipation	T _C =25°C	5	75	14/
	Tc=100°C	PD	38	W
Continuous Drain Current ^(Note 4)	T _A =25 [°] C		-14	Δ
	T _A =70°C	I _D	-11.7	A
Power Discinction	T _A =25 [°] C	De	3.3	W
Power Dissipation	T _A =70 [°] C	PD	2.3	VV
Single Pulse Avalanche Energy ^{(Note}	9 5)	Eas	132	mJ
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~175	°C
Thermal Resistance ^(Note 4)	Junction to Case	R _{θJC}	2	°C/W
	Junction to Ambient	R _{θJA}	45	C/W



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Electrical Characteristics (TA=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_{D} =-250uA	-40	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.9	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A	-	7.5	9.4		
		V _{GS} =-4.5V, I _D =-10A	-	11	14.3	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-40V, V_{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA	
Dynamic ^(Note 6)	-		•	•			
Total Gate Charge	Qg		-	59	-		
Gate-Source Charge	Qgs	V _{DS} =-32V, I _D =-20A, V _{GS} =-10V	-	9	-	nC	
Gate-Drain Charge	Q _{gd}	VGS=-10V	-	20	-		
Input Capacitance	Ciss		-	3300	-		
Output Capacitance	Coss	V _{DS} =-25V, V _{GS} =0V, f=1MHz	-	380	-	pF	
Reverse Transfer Capacitance	Crss	I=IWHZ	-	240	-		
Gate resistance	Rg	f=1MHz	-	4	-	Ω	
Turn-On Delay Time	td _(on)		-	13	-		
Turn-On Rise Time	tr	V _{DS} =-32, I _D =-20A,	-	16	-		
Turn-Off Delay Time	td _(off)	V _{GS} =-10V, R _G =3Ω	-	54	-	ns	
Turn-Off Fall Time	tf		-	33	-		
Drain-Source Diode							
Diode Forward Current	Is	Tc=25°C	-	-	-67	•	
Pulsed Diode Forward Current	I _{SM}	1c=25 C	-	-	-228	A	
Diode Forward Voltage	V _{SD}	Is=-20A, V _{GS} =0V	-	-0.85	-1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =-20A	-	23	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	11	-	nC	

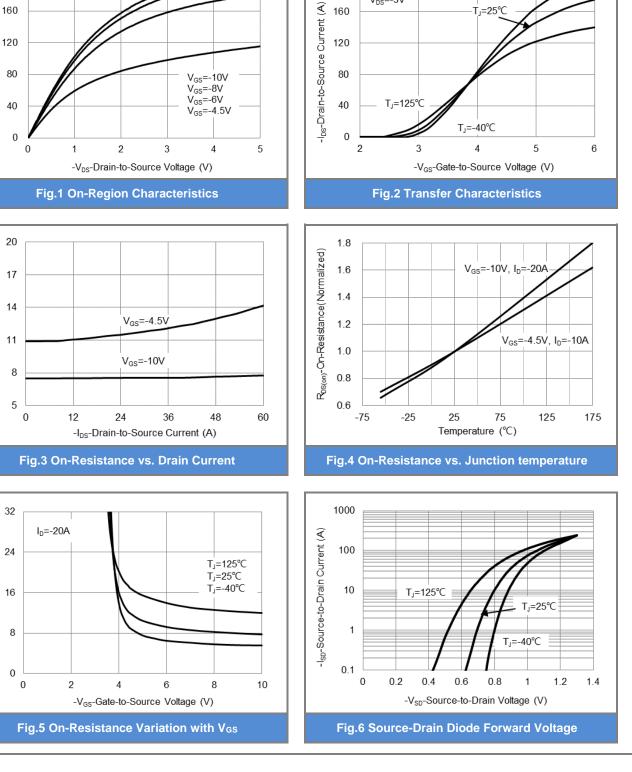
NOTES :

- 1. Pulse width<u><</u>300us, Duty cycle<u><</u>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS} =-23A, V_{DD} =-30V, V_{GS} =-10V, Starting T_J=25°C.
- 6. Guaranteed by design, not subject to production testing.

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 $R_{\text{DS(on)}}$ -On-Resistance (m Ω)

PJQ5451E-AU-REV.00



200

160

120

80

40

V_{DS}=-3V

TJ=125℃

T,=25℃

TYPICAL CHARACTERISTIC CURVES

200 -I_{DS}-Drain-to-Source Current (A) 160 120 80 V_{GS}=-10V V_{GS}=-8V V_{GS}=-6V 40

PJQ5451E-AU

PANJ SEM CONDUCTOR

g

Ros(on)-On-Resistance



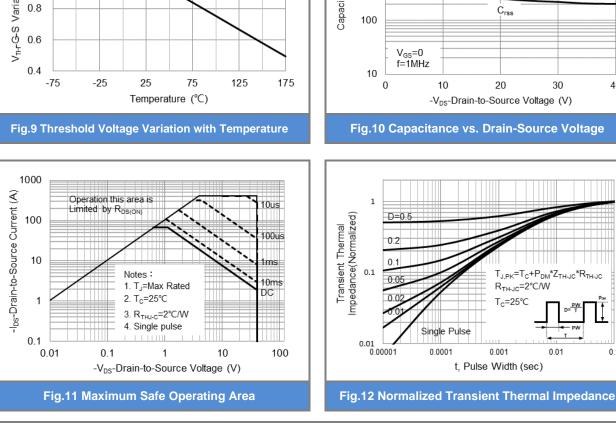
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0.1

40

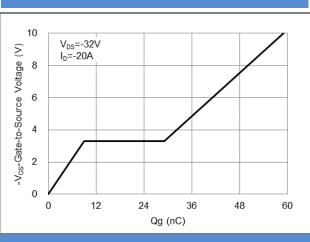


TYPICAL CHARACTERISTIC CURVES

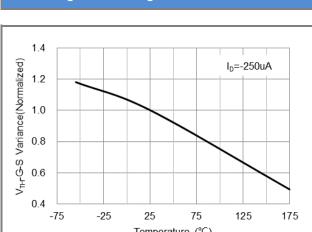
PANJ

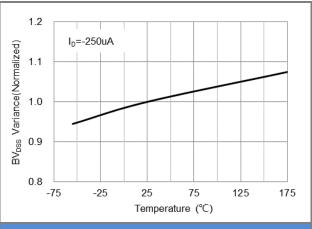
SEM CONDUCTOR

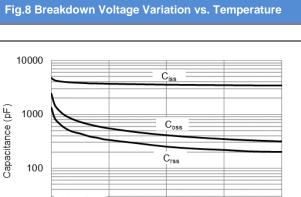
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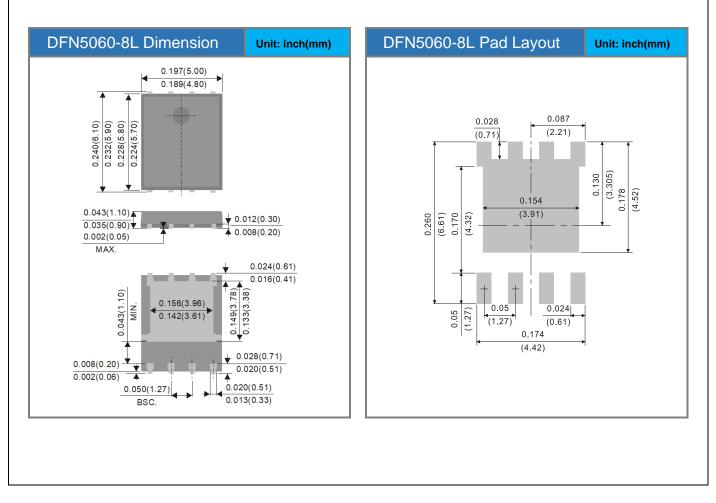


PJQ5451E-AU

Product and Packing Information

Part No.	Package Type Packing Type		Marking
PJQ5451E-AU	DFN5060-8L	3K pcs / 13" reel	Q5451E

Packaging Information & Mounting Pad Layout





PJQ5451E-AU

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